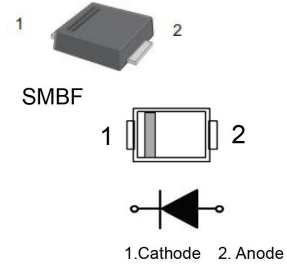



**Features:**

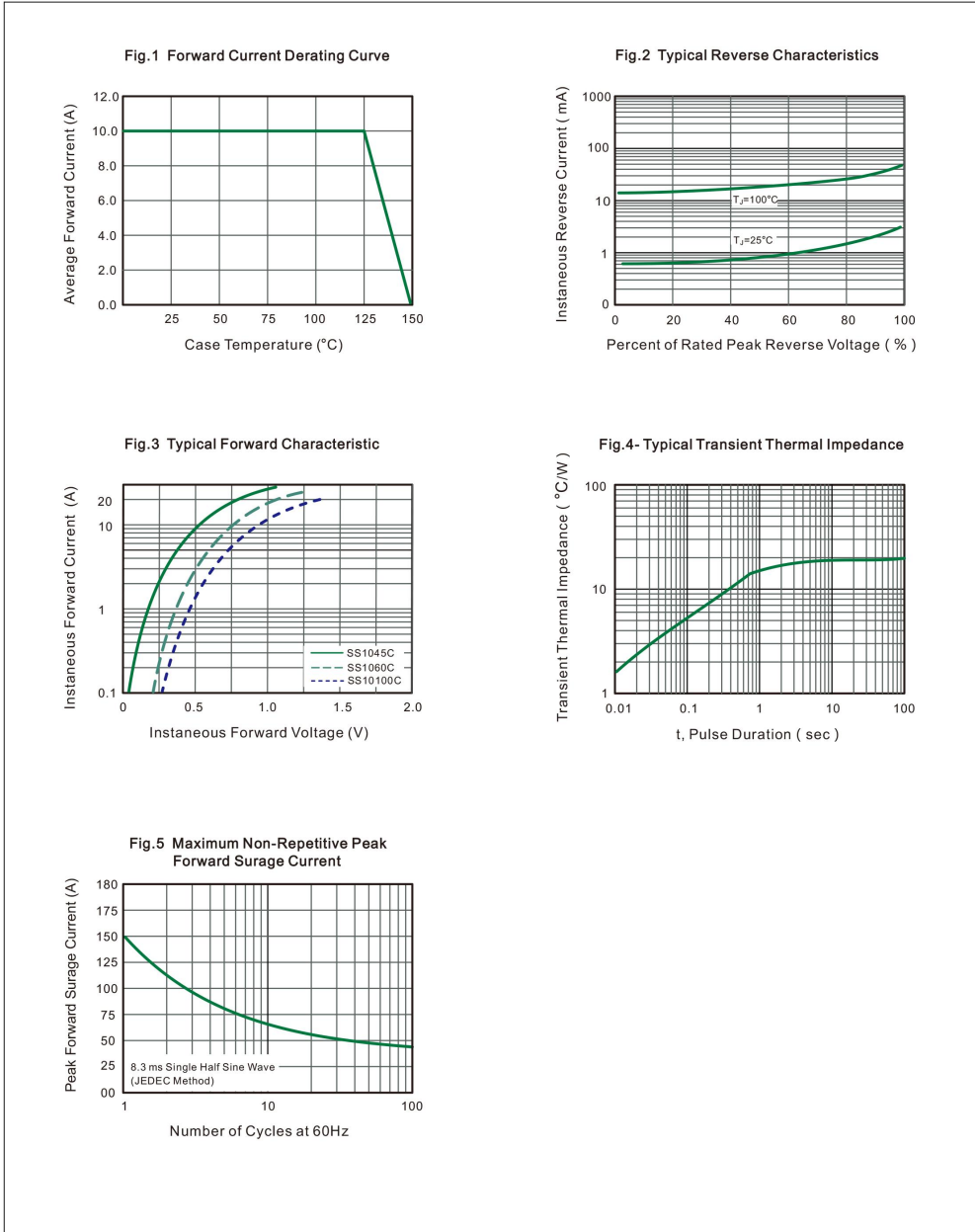
- Metal silicon junction, majority carrier conduction
- For surface mounted applications
- Low power loss, high efficiency
- Fast switching for high efficiency
- High forward surge current capability
- For use in low voltage, high frequency inverters

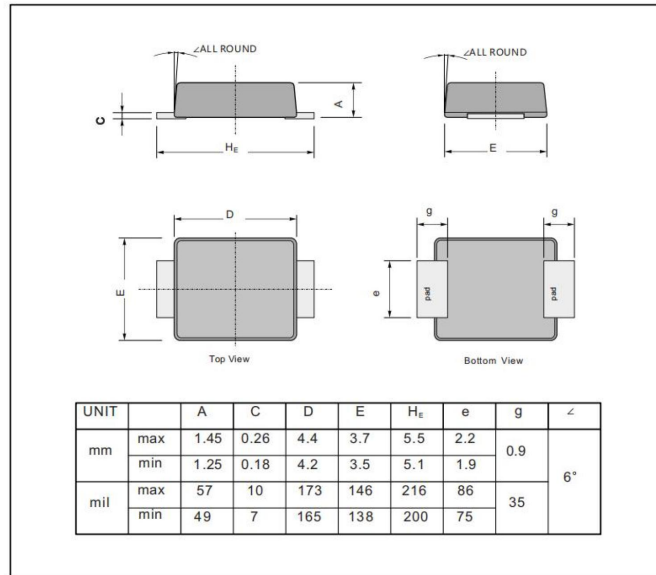

**Absolute Maximum Ratings\* (TA=25°C Unless otherwise noted)**

Ratings at 25 °C ambient temperature unless otherwise specified. Single phase, half wave, 60Hz resistive or inductive load, for capacitive load, derate by 20 %

Parameter	Symbols	CH1045BF	CH1060BF	CH10100BF	Units
Maximum Repetitive Peak Reverse Voltage	$V_{RRM}$	45	60	100	V
Maximum RMS voltage	$V_{RMS}$	32	42	70	V
Maximum DC Blocking Voltage	$V_{DC}$	45	60	100	V
Maximum Average Forward Rectified Current	$I_{F(AV)}$	10.0			A
Peak Forward Surge Current, 8.3ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	$I_{FSM}$	150			A
Max Instantaneous Forward Voltage @10.0 A	$V_F$	0.55	0.70	0.85	V
Maximum DC Reverse Current at Rated DC Reverse Voltage	$I_R$	0.5 10			mA
Typical Thermal Resistance	$R_{\theta JA}$	35			°C/W
Operating Junction Temperature Range	$T_J$	-55 ~ +150			°C
Storage Temperature Range	$T_{stg}$	-55 ~ +150			°C

( 1 ) P.C.B. mounted with 2.0" X 2.0" (5 X 5 cm) copper pad areas.

**Typical Characteristics**


**Package Dimension**
**SMBF**

**The recommended mounting pad size**
